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<b>Session Title:</b>	<b>26. Oxide TFT Reliability</b>
<b>Date:</b>	Aug. 24, 2016 (Wednesday)
<b>Time:</b>	16:30~17:40
<b>Room</b>	Room B (Halla B)
<b>Session Chairs</b>	Prof. Lei Wang (South China Univ. of Technology, China) Dr. Jun Hyung Lim (Samsung Display Co., Ltd., Korea)

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B26-1

16:30~16:55

### **[Invited] Theory of Defects and Doping in Wide-Band-Gap Oxides**

Anderson Janotti (Univ. of Delaware, U.S.A.)

B26-2

16:55~17:10

### **Analysis on Light Propagation into InGaZnO Thin-Film Transistors**

Saeroonter Oh (Hanyang Univ., Korea), Jong Uk Bae, Kwon-Shik Park, Soo-Young Yoon, and In Byeong Kang (LG Display Co., Ltd., Korea)

B26-3

17:10~17:25

### **Significant Sheet Resistance Reduction of a-IGZO via Low Temperature Excimer Laser Irradiation**

Juan Paolo Bermundo, Yasuaki Ishikawa, Mami N. Fujii (Nara Inst. of Science and Tech., Japan), Hiroshi Ikenoue (Kyushu Univ., Japan), and Yukiharu Uraoka (Nara Inst. of Science and Tech., Japan)

B26-4

17:25~17:40

### **Temperature-Dependency of the Donor Creation under Positive Gate and Drain Bias Stress in Self-Aligned Top-Gate a-InZnO TFTs**

Sungju Choi, Jonghwa Kim, Jungmok Kim, Jun Tae Jang, Hara Kang, Jea-Young Kim, Daehyun Ko, Dong Myong Kim, Sung-Jin Choi (Kookmin Univ., Korea), Jae Chul Park (Samsung Advanced Inst. of Tech., Korea), and Dae Hwan Kim (Kookmin Univ., Korea)